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Sheet 1 of 1

Complete if Known	
Application Number	10/626,718
Filing Date	July 25, 2003
First Named Inventor	MIURA et al.
Art Unit	Unassigned 2818
Examiner Name	Unassigned LONG TRAN
Attorney Docket Number	300.33045CC3

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
LT		US-4,839,308	06/1989	Wakamatsu	
LT		US-4,842,675	06/1989	Chapman et al.	
LT		US-4,860,070	08/1989	Arimoto et al.	
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Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3]-Number[4]-Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Country	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
LT		JP 3-96249	04/1991	Japan (Abstract only)		
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Chiu et al., "A Bird's Beak Free Local Oxidation Technology Feasible for VLSI Circuits Fabrication", IEEE TRANSACTIONS ON ELECTRON DEVICES, Vo. ED-29, No. 4, 1983, pages 536-540

Examiner Signature	LONG TRAN	Date Considered	11/01/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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